

SPECIFICATION

Device Name : IGBT Module

Type Name : 7MBR10SA060D-01

Spec. No. : MS6M 0540

Date : Jun. - 02 - 2000

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Fuji Electric Co., Ltd.
Matsumoto Factory

	DATE	NAME	APPROVED	Fuji Electric Co., Ltd.	
DRAWN	Jun. - 2 - '00	T. Kobayashi		DWG NO	MS6M 0540
CHECKED	June - 2 - 00	S. Kiyota			
			T. Miyasaka		



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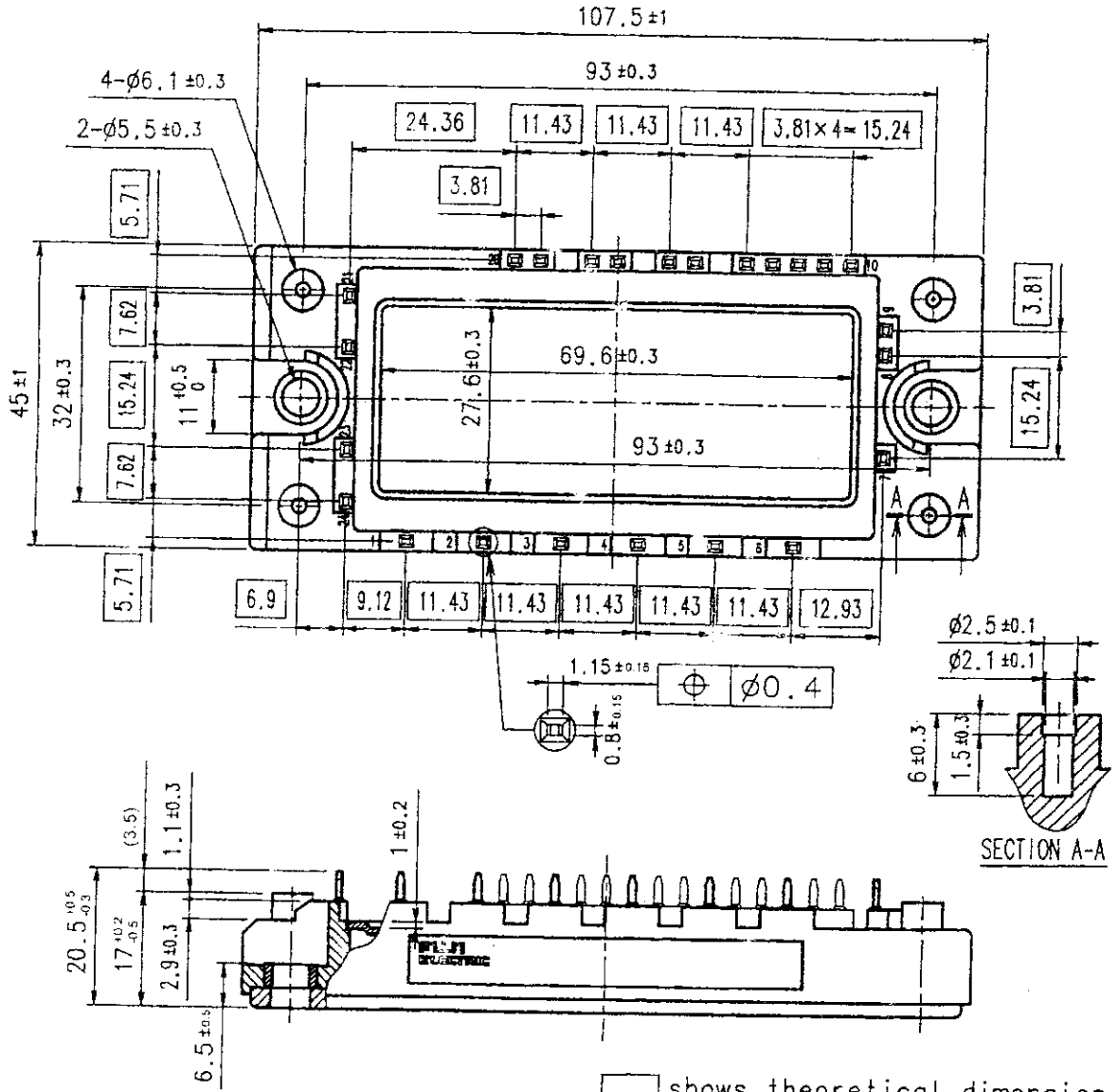
Revised Records

Date	Classi- fication	Ind.	Content	Applied date	Drawn	Checked	Approved
Jan - 2 - '99	enactment	—	—	Issued date	—	S. Mytka	T. Mytka

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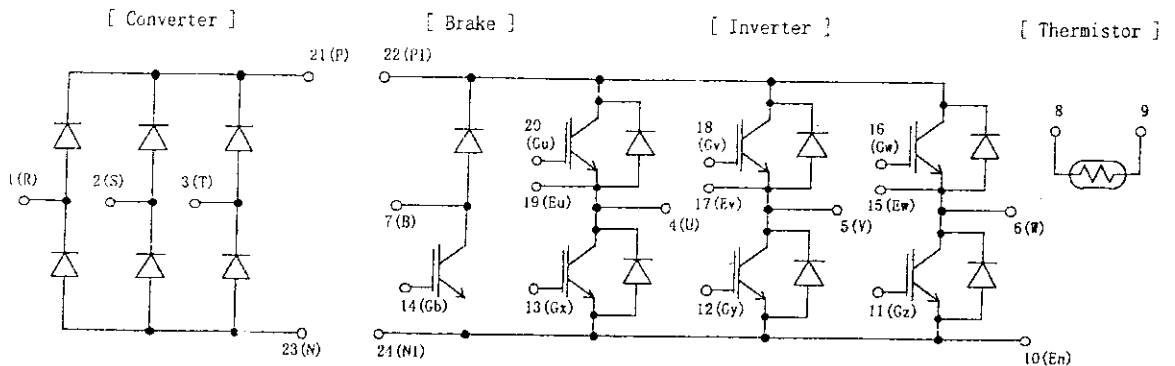
7MBR10SA060D-01

1. Outline Drawing (Unit : mm)



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2. Equivalent circuit



3. Absolute Maximum Ratings (at Tc= 25C unless otherwise specified)

Items		Symbols	Conditions	Maximum Ratings	Units
Inverter	Collector-Emitter voltage	VCES		600	V
	Gate-Emitter voltage	VGES		+20	V
	Collector current	Ic	Continuous	20	A
		Icp	1ms	40	A
		-Ic		20	A
Collector Power Dissipation	Pc	1 device	80	W	
Brake	Collector-Emitter voltage	VCES		600	V
	Gate-Emitter voltage	VGES		+20	V
	Collector current	Ic	Continuous	20	A
		Icp	1ms	40	A
	Collector Power Dissipation	Pc	1 device	50	W
	Repetitive peak reverse Voltage(Diode)	VRRM		600	V
Converter	Repetitive peak reverse Voltage	VRRM		800	V
	Average Output Current	Io	50Hz/60Hz sine wave	25	A
	Surge Current (Non-Repetitive)	IFSM	Tj=150C, 10ms	260	A
	I ² t (Non-Repetitive)	I ² t	half sine wave	338	A ² s
Junction temperature	Tj		150	C	
Storage temperature	Tstg		-40~ +125	C	
Isolation voltage:	between terminal and copper base ^{(*)1}	Viso	AC : 1min.	2500	V
	between thermistor and others ^{(*)2}			2500	V
Mounting Screw Torque ^{(*)3}				3.5	Nm

(*)1 All terminals should be connected together when isolation test will be done.

(*)2 Terminal 8 and 9 should be connected together. Terminal 1 to 7 and 10 to 24 should be connected together and shorted to copper base.

(*)3 Recommendable Value : 2.5~3.5 Nm (M5)

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4. Electrical characteristics (at $T_j = 25\text{C}$ unless otherwise specified)

Items	Symbols	Conditions	Characteristics			Units					
			min.	typ.	Max.						
Inverter	Zero gate voltage Collector current	ICES	VGE	0 V, VCE	600 V	1.0	mA				
	Gate-Emitter leakage current	IGES	VCE	0 V, VGE	+20 V	200	nA				
	Gate-Emitter threshold voltage	VGE(th)	VCE	20 V, Ic =	20 mA	5.5	7.8	8.5	V		
	Collector-Emitter saturation voltage	VCE(sat)	VGE	15 V, Ic =	20 A	chip	1.8		V		
						terminal	1.95	2.4			
	Input capacitance	Cies	VGE	0 V, VCE	10 V		3000		pF		
	Turn-on time	ton	Vcc=	300 V	Ic =	20 A	VGE	+-15 V	0.45	1.2	us
									0.25	0.6	
									0.08		
	Turn-off time	toff	RG =	120 ohm	VGE	+-15 V	VGE	+-15 V	0.40	1.0	us
0.05									0.35		
Forward on voltage	VF	IF =	20 A	VGE	+-15 V	chip	1.8		V		
						terminal	1.95	2.6			
Reverse recovery time	trr	IF =	20 A					300	ns		
Brake	Zero gate voltage Collector current	ICES	VGE	0 V, VCE	600 V	1.0	mA				
	Gate-Emitter leakage current	IGES	VCE	0 V, VGE	+20 V	200	nA				
	Collector-Emitter saturation voltage	VCE(sat)	VGE	15 V, Ic =	20 A	chip	1.8		V		
						terminal	1.95	2.4			
	Turn-on time	ton	Vcc=	300 V	Ic =	20 A	VGE	+-15 V	0.45	1.2	us
									0.25	0.6	
	Turn-off time	toff	RG =	120 ohm	VGE	+-15 V	VGE	+-15 V	0.40	1.0	us
0.05									0.35		
Reverse current	IRRM	VR =	600 V					1.0	mA		
Converter	VFM	IF =	20 A	VGE	+-15 V	chip	1.0		V		
						terminal	1.1	1.5			
Reverse current	IRRM	VR =	800 V					1.0	mA		
Thermistor	Resistance	R	T = 25C			5000		ohm			
			T = 100C			465	495		520		
	B value	B	T = 25/50C			3305	3375	3450	K		

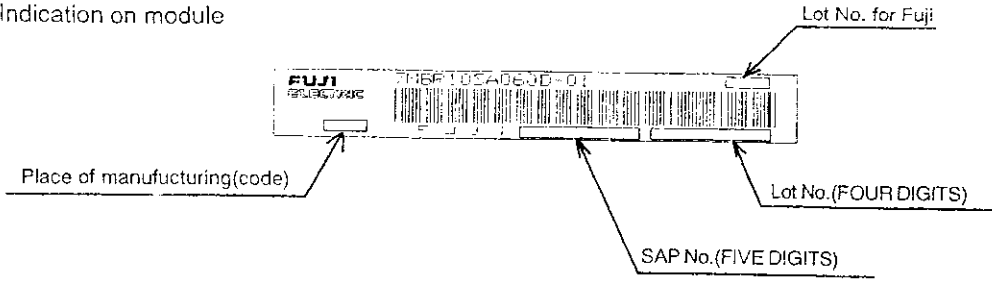
5. Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	Max.	
Thermal resistance (1 device)	Rth(j-c)	Inverter IGBT			1.56	C/W
		Inverter FWD			3.00	
		Brake IGBT			2.50	
		Converter Diode			1.30	
Contact Thermal resistance	Rth(c-f)	with Thermal Compound (*)		0.05		C/W

* This is the value which is defined mounting on the additional cooling fin with thermal compound.

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6. Indication on module



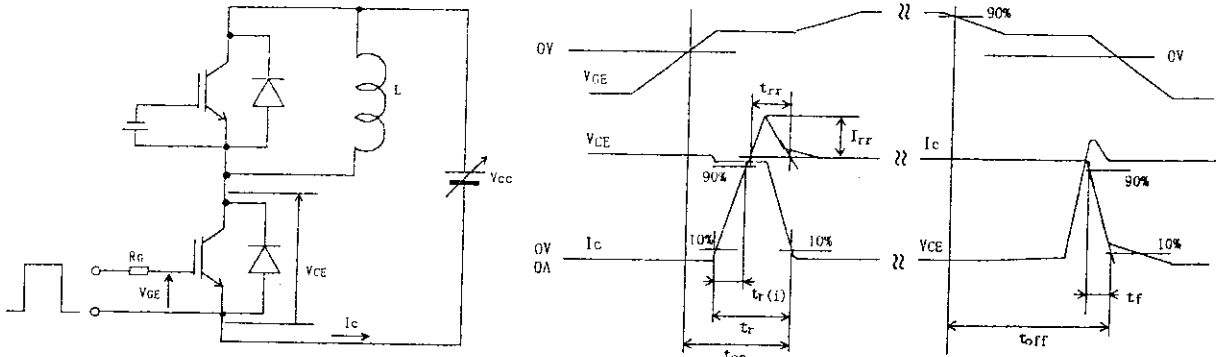
7. Applicable category

This specification is applied to Power Integrated Module named 7MBR10SA060D-01.

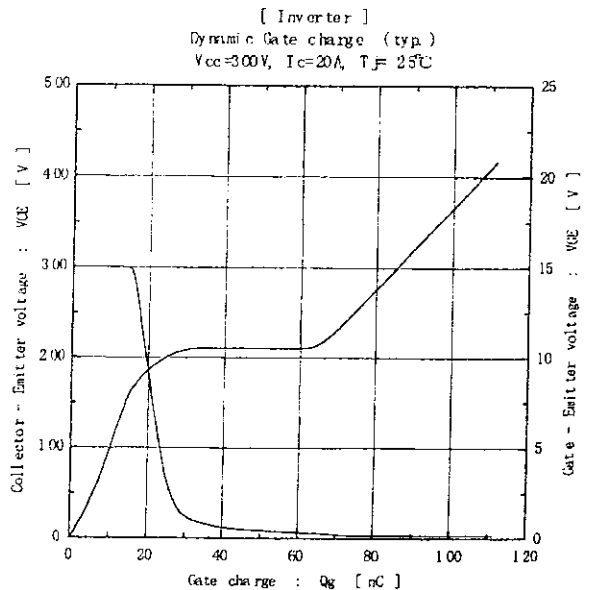
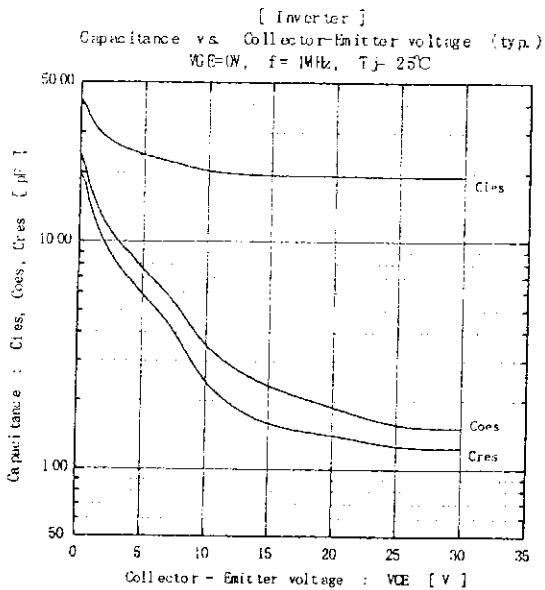
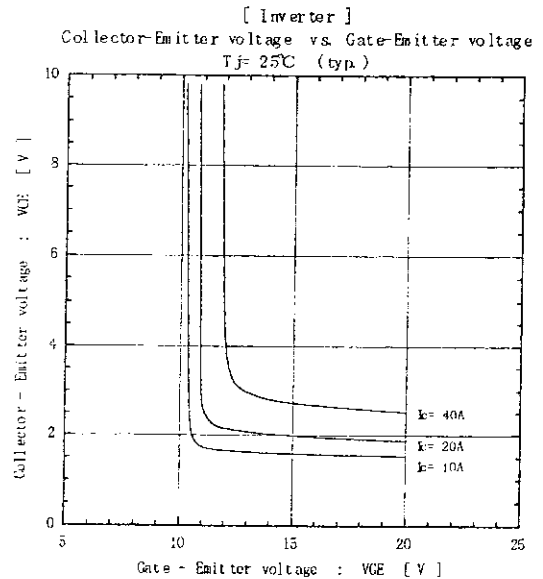
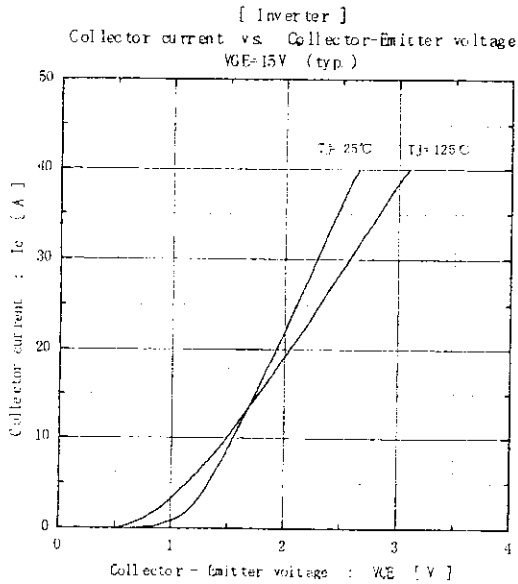
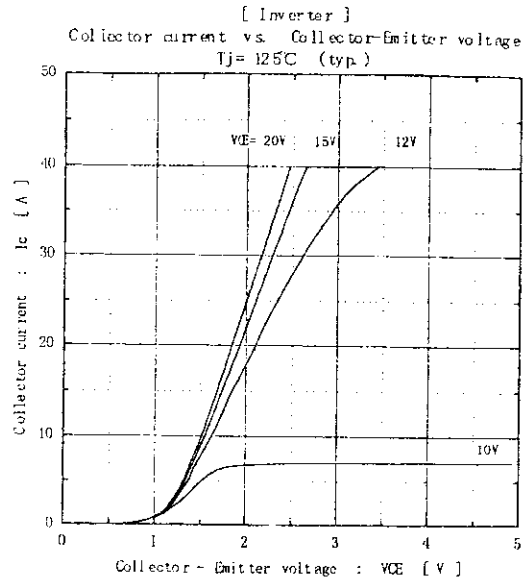
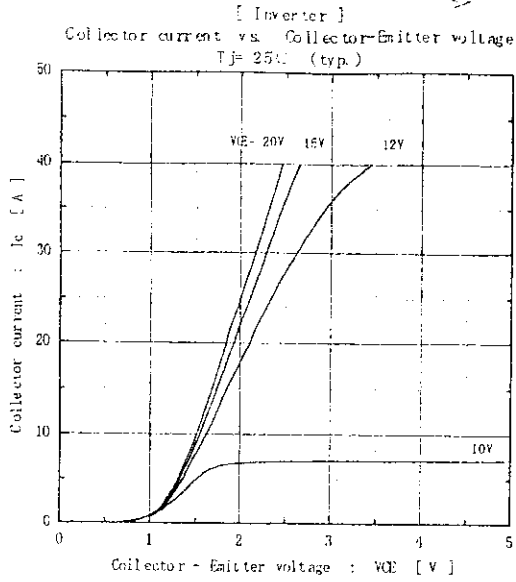
8. Storage and transportation notes

- The module should be stored at a standard temperature of 5 to 35°C and humidity of 45 to 75% .
- Store modules in a place with few temperature changes in order to avoid condensation on the module surface.
- Avoid exposure to corrosive gases and dust.
- Avoid excessive external force on the module.
- Store modules with unprocessed terminals.
- Do not drop or otherwise shock the modules when transporting.
- Please connect adequate fuse or protector of circuit between three-phase line and this product to prevent the equipment from causing secondary destruction.

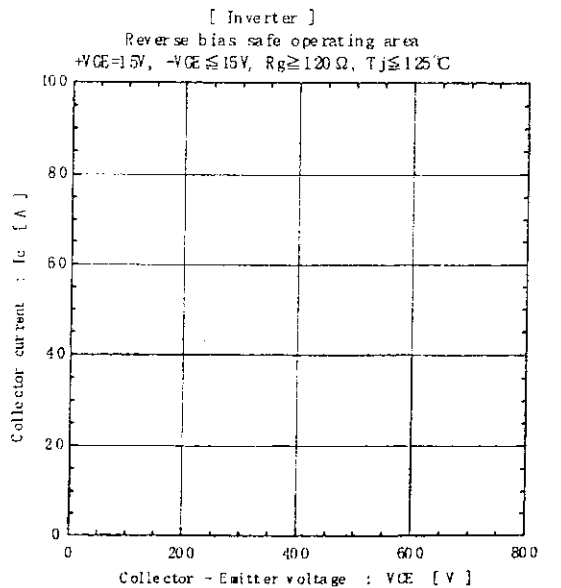
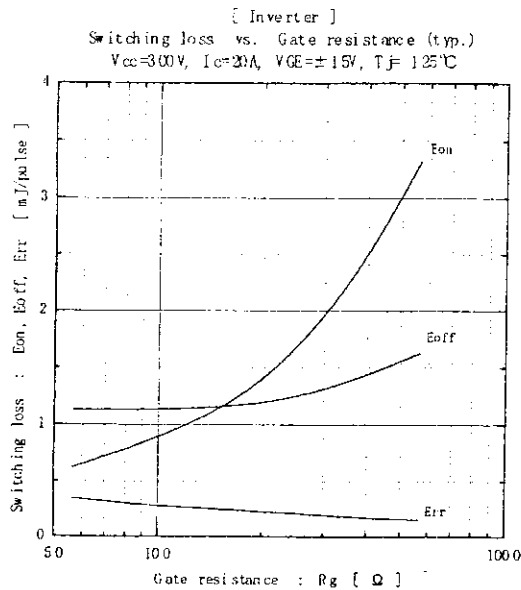
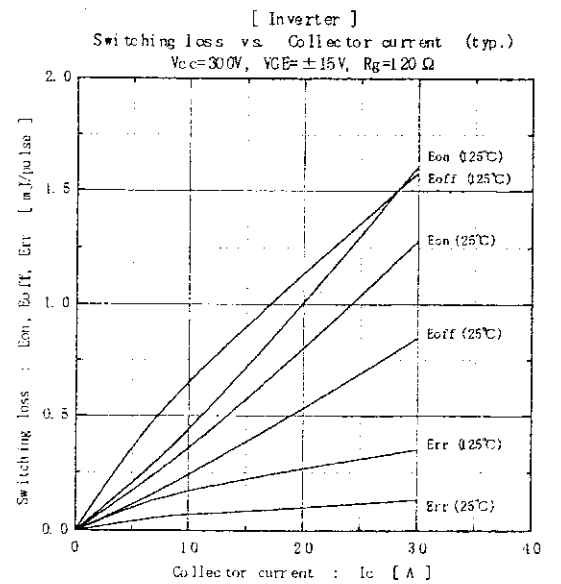
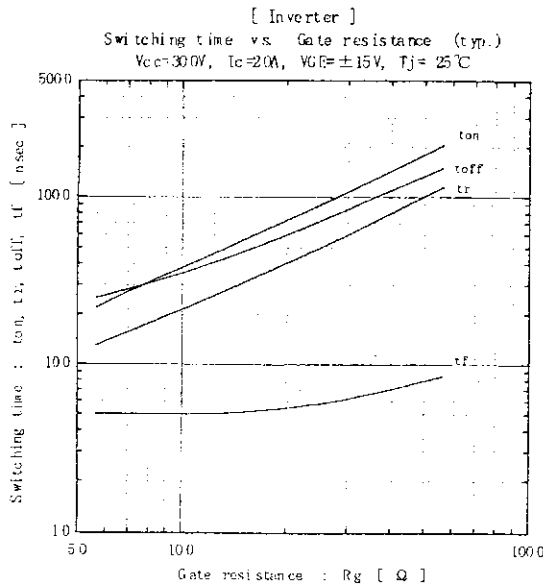
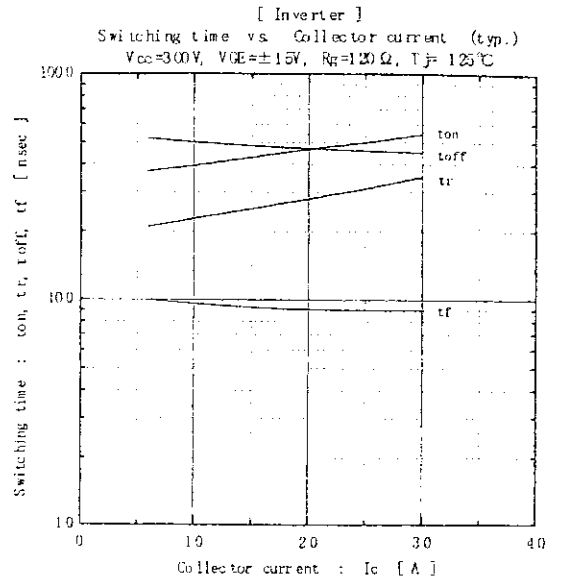
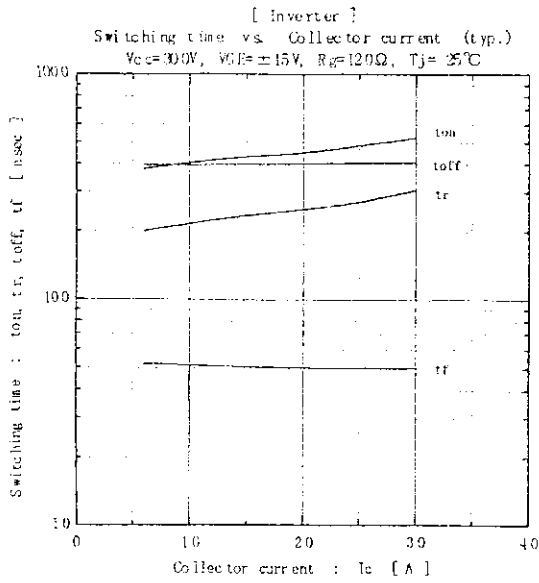
9. Definitions of switching time



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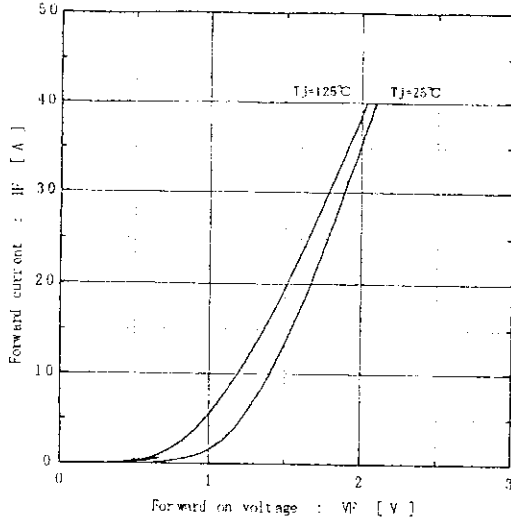


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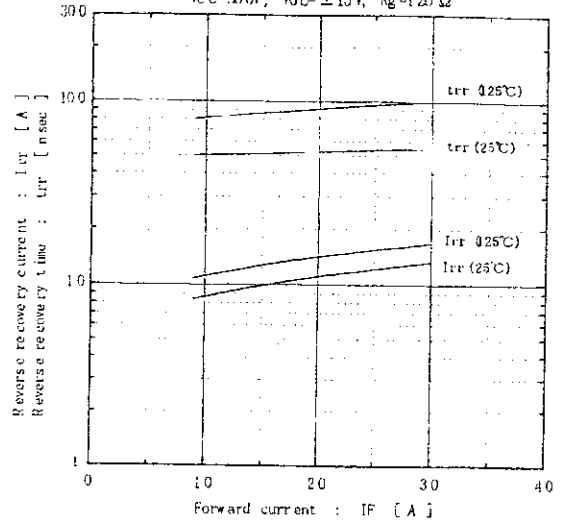


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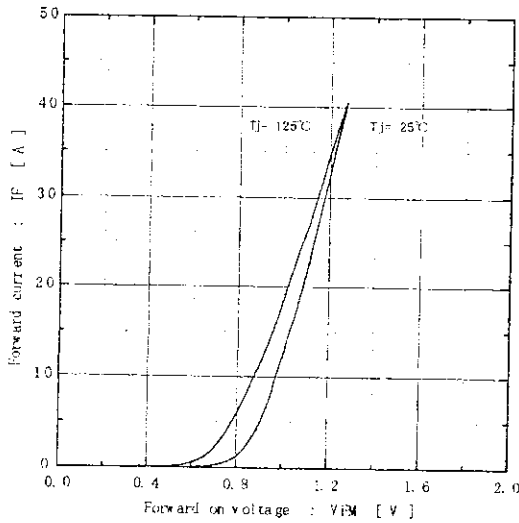
[Inverter]
Forward current vs. Forward on voltage (Typ.)



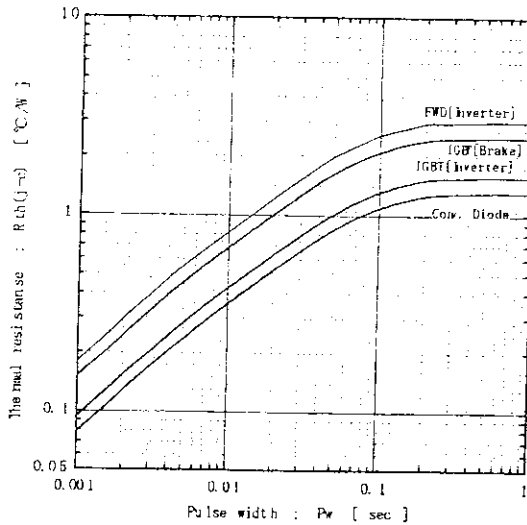
[Inverter]
Reverse recovery characteristics (Typ.)
 $V_C = 300\text{V}$, $V_{GE} = \pm 15\text{V}$, $R_g = 120\ \Omega$



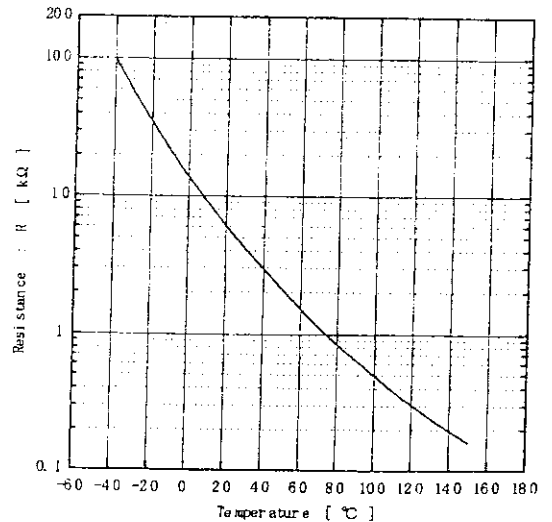
[Converter]
Forward current vs. Forward on voltage (Typ.)



Transient thermal resistance

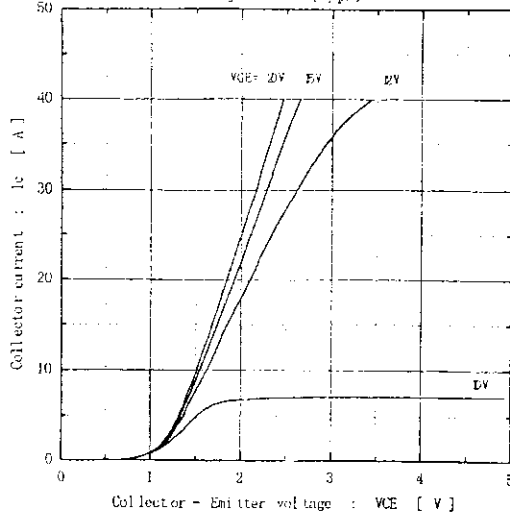


[Thermistor]
Temperature characteristic (Typ.)

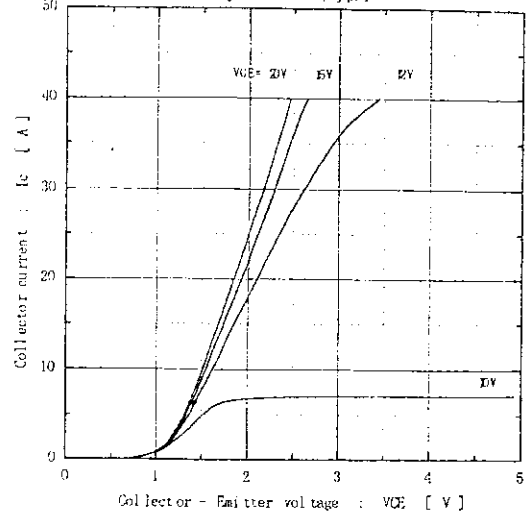


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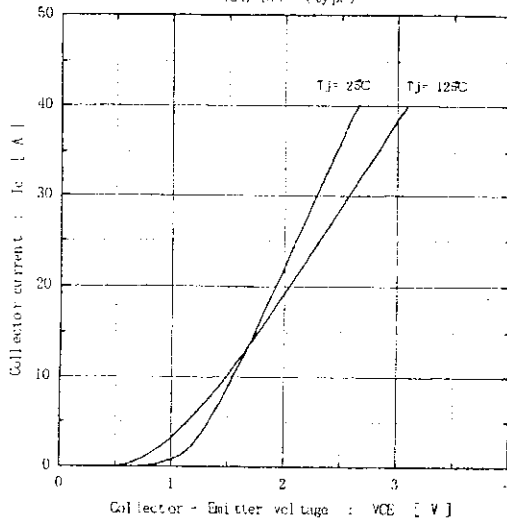
[Brake]
Collector current vs. Collector-Emitter voltage
 $T_J = 25^\circ\text{C}$ (typ.)



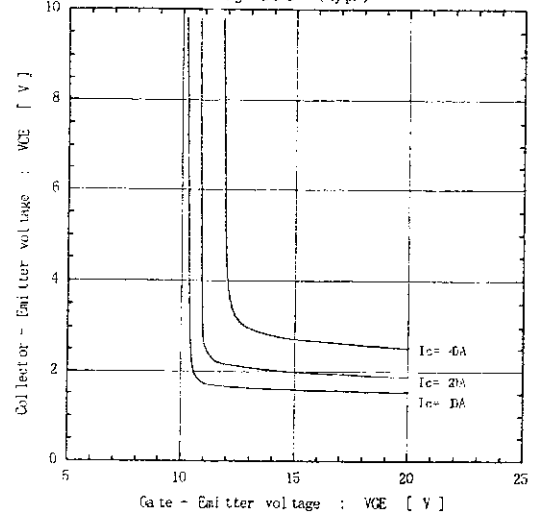
[Brake]
Collector current vs. Collector-Emitter voltage
 $T_J = 125^\circ\text{C}$ (typ.)



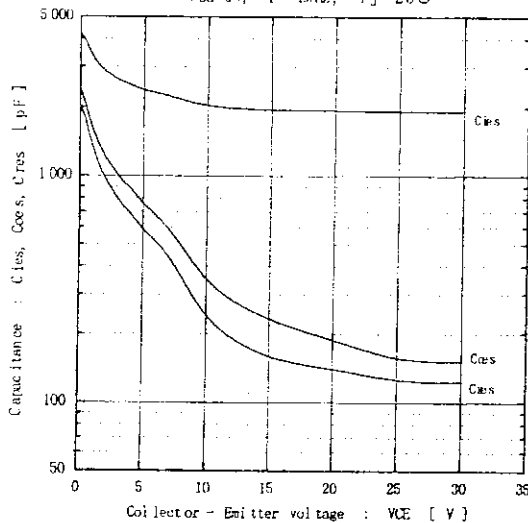
[Brake]
Collector current vs. Collector-Emitter voltage
 $V_{GE} = 15\text{V}$ (typ.)



[Brake]
Collector-Emitter voltage vs. Gate-Emitter voltage
 $T_J = 25^\circ\text{C}$ (typ.)



[Brake]
Capacitance vs. Collector-Emitter voltage (typ.)
 $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$, $T_J = 25^\circ\text{C}$



[Brake]
Dynamic Gate charge (typ.)
 $V_{ce} = 300\text{V}$, $I_c = 20\text{A}$, $T_J = 25^\circ\text{C}$

